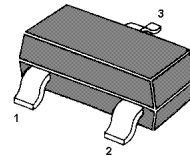


## SOT-23 Plastic-Encapsulate Transistors

**MMBT2907A** TRANSISTOR (PNP)

### FEATURES

- Epitaxial planar die construction
- Complementary NPN Type available(MMBT2222A)



1. Base 2. Emitter 3. Collector  
SOT-23 Plastic Package

**Marking: 2F**

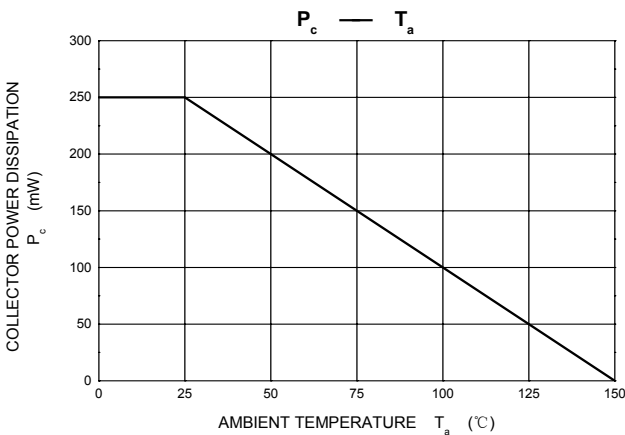
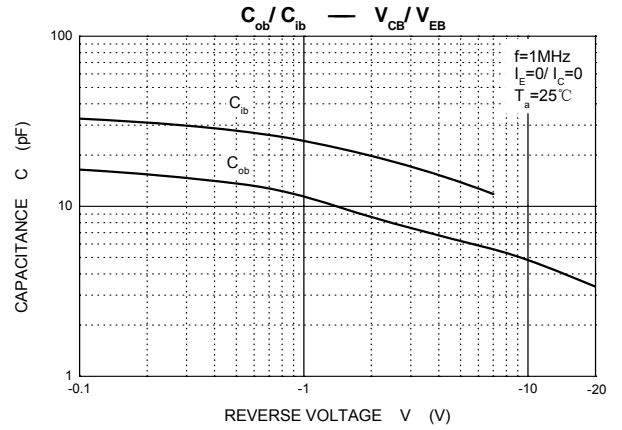
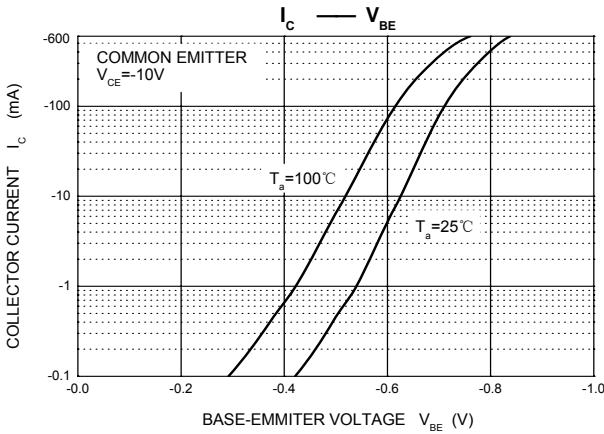
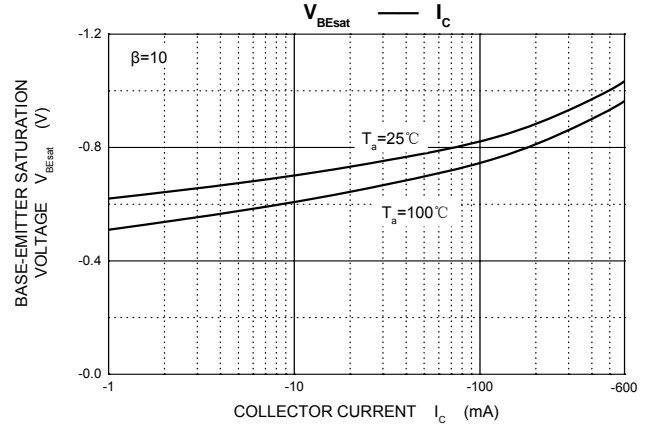
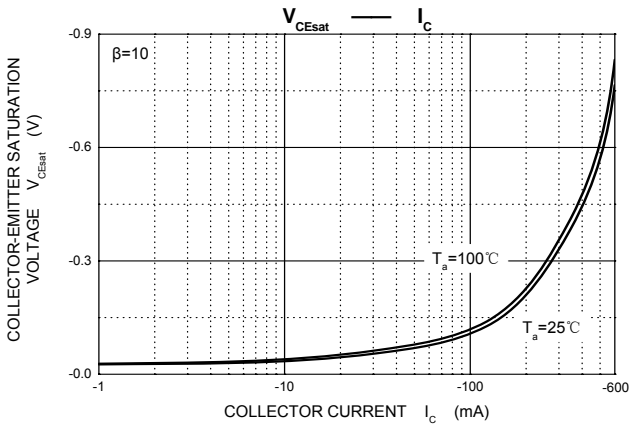
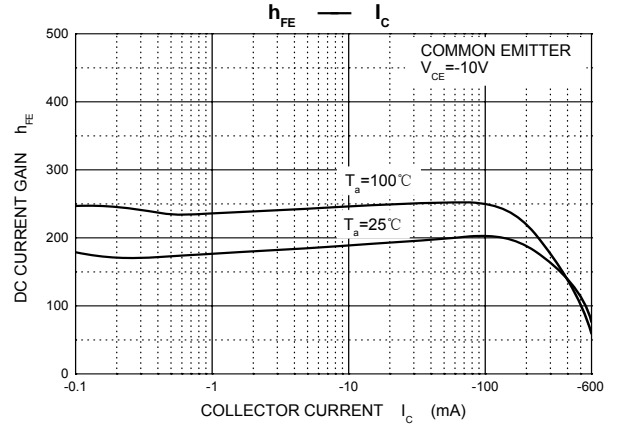
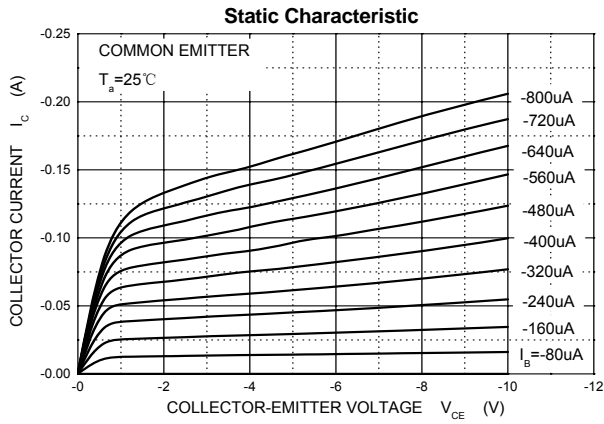
### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-60	V
$V_{CE0}$	Collector-Emitter Voltage	-60	V
$V_{EB0}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current -Continuous	-600	mA
$P_D$	Total Device Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	500	$^{\circ}\text{C}/\text{W}$
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55 to +150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_c=-10\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_c=-10\text{mA}, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=-10\mu\text{A}, I_c=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-10	nA
DC current gain	$h_{FE(1)}$ *	$V_{CE}=-10\text{V}, I_c=-0.1\text{mA}$	75			
	$h_{FE(2)}$ *	$V_{CE}=-10\text{V}, I_c=-1\text{mA}$	100			
	$h_{FE(3)}$ *	$V_{CE}=-10\text{V}, I_c=-10\text{mA}$	100			
	$h_{FE(4)}$ *	$V_{CE}=-10\text{V}, I_c=-150\text{mA}$	100		300	
	$h_{FE(5)}$ *	$V_{CE}=-10\text{V}, I_c=-500\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	$I_c=-150\text{mA}, I_B=-15\text{mA}$			-0.4	V
	$V_{CE(sat)}$ *	$I_c=-500\text{mA}, I_B=-50\text{mA}$			-1.60	V
Base-emitter saturation voltage	$V_{BE(sat)}$ *	$I_c=-150\text{mA}, I_B=-15\text{mA}$			-1	V
	$V_{BE(sat)}$ *	$I_c=-500\text{mA}, I_B=-50\text{mA}$			-2.6	V
Transition frequency	$f_T$	$V_{CE}=-20\text{V}, I_c=-50\text{mA}, f=100\text{MHz}$	200			MHz
Delay time	$t_d$	$V_{CE}=-30\text{V}, I_c=-150\text{mA}, I_{B1}=-15\text{mA}$			10	ns
Rise time	$t_r$				40	ns
Storage time	$t_s$	$V_{CE}=-6\text{V}, I_c=-150\text{mA}, I_{B1}=-I_{B2}=-15\text{mA}$			80	ns
Fall time	$t_f$				30	ns

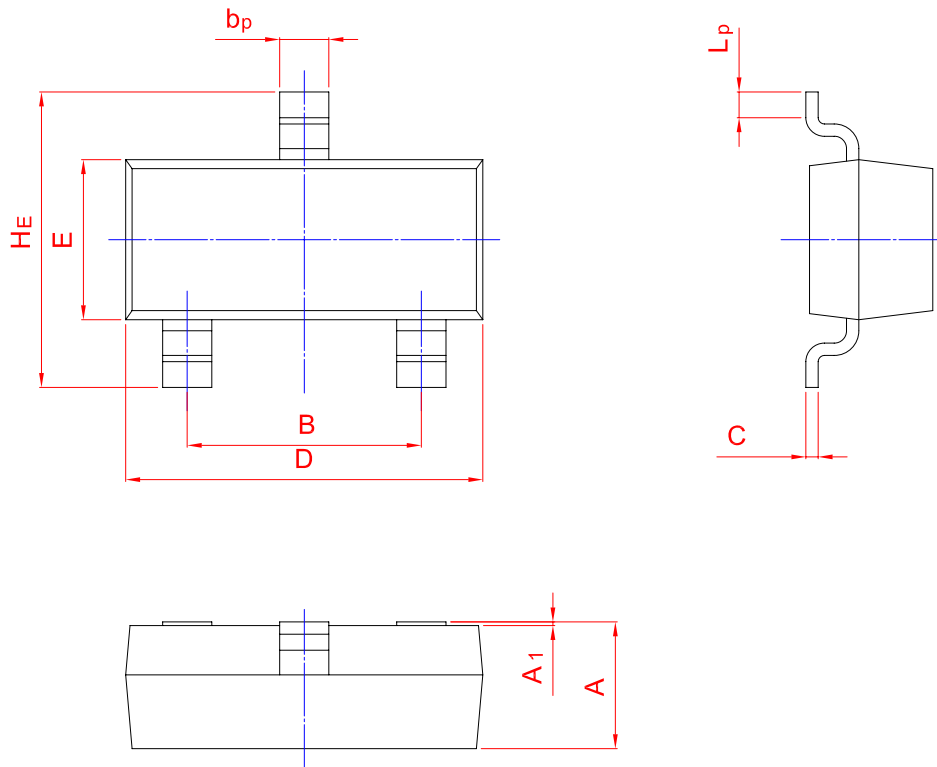
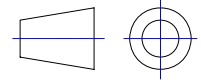
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	$b_p$	C	D	E	$H_E$	$A_1$	$L_p$
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)